

PATENT APPLICATION

Atty. Docket No.: 8371-129

Serial No.: Not Yet Known

Applicant: Apostolos VOUTSAS and Yukihiro NAKATA

Filing Date: Not Yet Known

Group: Not Yet Known

2823



INFORMATION DISCLOSURE CITATION FORM PTO-1449 (Modified)

OTHER DOCUMENTS

Exam Init	Ref	(Including Author, Title, Date, Pertinent Pages, Etc.)
	G	Takashi Serakawa, Seiiti Shirai, Akio Okamoto and Shiro Suyama, <i>Low-Temperature Fabrication of High-Mobility Poly-Si TFT's For Large-Area LCS's</i> , 1998, <u>IEEE Transactions of Electron Devices</u> , Vol. 36, pp 1929-1933
	G	Shiro Suyama, Akio Okamoto and Tadashi Serikawa, <i>Electrical Characteristics of MOSFET's Utilizing Oxygen-Argon Sputter-Deposited Gate Oxide Films</i> , 1987, <u>IEEE Transactions on Electron Devices</u> , Vol. ED-34, No.10, pp 2124-2128
	G	T. Serikawa and A. Okamoto, <i>Properties of Magnetron-Sputtered Silicon Nitride Films</i> , 1984 J. Electrochem.Soc: Solid State Science and Technology, Vol. 131, No. 12, pp 2928-2933
	G	G.K. Giust, T.W. Sigmon, P.G. Carey, B. Weiss, G.A. Davis, <i>Low-Temperature Polysilicon Thin-Film Transistors Fabricated from Laser-Processed Sputtered-Silicon Films</i> , 1998 <u>Electron Device Letters</u> , Vol. 19, No. 9, pp343-344
	G	D.P. Gosain and S. Usui, <i>Poly-Si TFT Fabrication and Hydrogenation Using a Process Compatible With Plastic Substrates</i> , <u>Electrochemical Society Proceedings</u> Vol. 98-22, pp 174-184
	G	F. Okumura and K. Yuda, <i>High-Quality Low-Temperature Gate Oxide For Poly-Si TFT's</i> , <u>Electrochemical Society Proceedings</u> , Vol. 98-22, pp 133-142

G

S./ Kawamura, T. Nishibe, N. Ibaraki, P-2: *Back-Channel Effects on the Threshold Voltage of Low-Temperature Poly-Si TFTs with SiN_x/Si₂ Dual Under Layer*, 1999 SID 99 DIGEST, pp 456-459

Examiner: _____

FOURSON

Date Considered: _____

2/22/03